

In all investigations concerning pressure influence on superconductor main attention is given to the change of the critical temperature T_c and critical magnetic field H_c [3]. In [4] it was considered that $2 \Delta/kT_c$ does not change with pressure.

One of the direct experimental methods for the study of the energy gap in superconductors is the electron tunnelling technique. Possibilities of the finest instrument allowed to find out a change of $2 \Delta/kT_c$ with pressure are given for Pb [5] and then less for Sn [6].

This paper presents results on tunnelling investigations of the energy gap in In and Tl under pressure.

2. Experimental Technique

2.1 Samples

As is known [7] the best gaps can be obtained on superconductor-barrier superconductor tunnel systems. This made superconducting diodes useful for investigations under pressure. Of all systems investigated the best are prepared on Al base, i.e. an Al-Al₂O₃ superconductor.

Al-I-In and Al-I-Tl samples were prepared by deposition in high (1×10^{-6} Torr) vacuum on a cooled (up to 80 to 100 °K) glass slide 4×16 mm². There were three junctions on one slide, each $1_{Al} \times 0.5_{In, Tl}$ mm² (Fig. 1). To avoid edge effects films were deposited through stencils supported by an electromagnet. Junction quality in the sense of fitness for their use in pressure measurements much depended on condensation and oxidation conditions of the Al film. Aluminium was sprayed from a tungsten U-vaporizer. During deposition the vacuum did not become worse due to preliminary long annealing (up to vacuum restoration) of the vaporizer and the hinge. Oxidation took place in the atmosphere of dry air at a pressure of 0.2 Torr for 5 min. Sample preparation was controlled by film and junction resistance measurements both during deposition and subsequent heating up to room temperatures. Junctions with resistance 50 to 100 Ω were chosen. Al-I-Tl samples were covered with Si monoxide of about 1 μ m thickness. In and Tl film thickness was determined by Linnik microinterferometer MII-4 and was equal to (1000 ± 100) Å. For Tl films $\frac{R_{300}}{R_{4.2}} = 14$ to 18.

Al films had resistivities of 4000 to 6400 Ω mm², and their initial critical temperature varied from 1.65 to 2 °K.

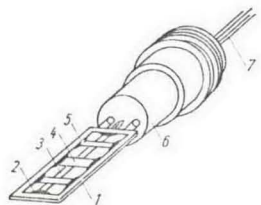


Fig. 1. Tunnel sample and obturator. 1 Sample holder made of getinax, 2 indium contacts, 3 Al film, 4 In and Tl films, 5 cover glass, 6 obturator, 7 electrical wires

2.2 High pressure technique

A high pressure bomb with kerosene-oil mixture [8] was used in all investigations. Pressure was created at room temperature and controlled by a hydraulic manometer. Here an almost linear change of tunnel junction resistance for $R(0) = 100 \Omega$, $dR/dp = 6 \Omega/\text{katm}$ was a reliable indication. Sensitivity of junction resistance to pressures gave the possibility of rejecting samples by immersing into liquid helium. The final pressure in the bomb at low temperatures was calculated from T_c changes of an In wire [9]:

$$T_c = 4.36 \times 10^{-5} p + 5.2 \times 10^{-10} p^2.$$

Electrical conductors were introduced into the obturator, this allowed measurements to be carried out simultaneously, by means of a 4-probe system, the critical temperature of films, the In wire, and corresponding tunnel characteristics.

2.3 Cryogenics and measuring apparatus

Low temperature measurements were carried out in a metal cryostat where it was possible to get temperatures from 4.2 to 1.15 °K. The bomb with samples was in liquid helium.

During the experiments the voltage-current characteristic was measured both at constant voltage and constant current conditions. Depending on the condition dI/dU or $(dU/dI)-U$ at a modulation frequency of 383 Hz were plotted. All tunnel characteristics were recorded automatically on a X-Y coordinate PP-09-type register. Constant voltage at a sample was measured by a high-impedance potentiometer to within $\approx 1 \mu\text{V}$ during recording.

3. Results and Discussion

Indium: After preparation Al-I-In samples were annealed for some days at room temperature. The critical temperature of In films practically did not differ from T_c^0 for massive pure indium. The halfwidth of the superconducting transition did not exceed 0.01 °K for all pressures. Table 1 gives the change of critical temperature for the film which is found to be

$$\frac{dT_c}{dp} = - (3.65 \pm 0.15) \times 10^{-5} \frac{^\circ\text{K}}{\text{atm}},$$

Table 1

T_c and 2Δ of indium under pressure

p (katm)	T_c (∓ 0.01 °K)	$t = \frac{T}{T_c}$	$2 \Delta(p, t)$ (∓ 0.01 meV)	$2 \Delta/kT_c^c$ (p, t)	$2 \Delta(p, 0)$ (meV)	$2 \Delta/kT_c^c$ ($p, 0$)
0	3.42	0.342	1.090	3.69	1.09	3.69
5	3.23	0.36	1.01	3.63	1.02	3.66
7	3.15	0.372	0.982	3.62	0.99	3.64
7.9	3.13	0.374	0.974	3.61	0.98	3.64
10.5	3.03	0.387	0.930	3.57	0.94	3.60
14	2.91	0.4	0.880	3.51	0.89	3.55